

ABSTRACT OF THE DISCLOSURE

Disclosed is a technique capable of improving a yield
of a semiconductor device by measuring a plurality of TEGs
arranged in a scribe region. A first electrode pad connected
5 to each terminal of a TEG is formed as a rectangular, minute,
isolated pattern having a side length of about 0.5 μm or
shorter and constituted of an uppermost layer wiring on a
semiconductor substrate, and therefore, a great number of TEGs
can be laid in a first scribe region. The characteristic
10 evaluation or the failure analysis is performed by contacting
a nanoprobe having a tip radius of curvature of 0.05 μm to 0.8
 μm to the first electrode pad.